# **RT2070T**

# 3 Channel DC-DC Converters +LDO +LSW PMIC with I<sup>2</sup>C Interface for Industrial and Automotive Application

### **General Description**

The RT2070T is a highly-integrated low-power highperformance analog SOC with PMIC (Power Management IC) in one single chip designed for Industrial/Automotive applications.

The RT2070T PMIC includes one high voltage synchronous step-down DC-DC converter, two low voltage synchronous step-down DC-DC converters, one low dropout LDO and one load switch with soft-start control and current limit. All MOSFETs are integrated, and compensation networks are built-in.

The RT2070T also uses I<sup>2</sup>C interface to set timing of power on/off, sequence and discharge function, and includes power good indicator (PGOOD).

The RT2070T is an Automotive-Grade Product that is AEC-Q100 Grade 1 Qualified and provides fault condition protections, including over-current protection, under-voltage lockout, over-voltage protection and over-temperature protection.

### Features

- Input Voltage Operating Range is 4.5V to 15V
- CH1 HV-Step-Down Regulator :  $V_{IN}$  Range is 4.5V to 15V
  - Support Up to 2A Loading With Up to 90% Efficiency
  - Switching Frequency is 2MHz
- CH2/3 LV Step-Down Regulator :  $V_{\text{IN}}$  Range is 2.7V to 5.5V
  - ▶ Support Up to 1A Loading, With Up to 90% Efficiency
  - Switching Frequency is 2MHz
- Linear Regulator : V<sub>IN</sub> Range is 2.7V to 5.5V
   Max Loading 0.5A
- Load Switch (LSW) : V<sub>IN</sub> Range is 2.7V to 5.5V
   Max Loading 0.5A
- Sequence Can be Controlled by Setting the Resistances of the SEQ Pin
- AEC-Q100 Grade 1 Qualified

### **Marking Information**

### Applications

- Industrial/Automotive Camera Module
- Car Infotainment

5P=YM DNN

5P= : Product Code YMDNN : Date Code

### **Simplified Application Circuit**





### **Ordering Information**

RT2070T 🗖 📮

Package Type QW : WQFN-24L 4x4 (W-Type) (Exposed Pad-Option 1)

Lead Plating System G : Green (Halogen Free and Pb Free)

Note :

Richtek products are :

- RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

**Functional Pin Description** 

### **Pin Configuration**



#### WQFN-24L 4X4

Pin No.	Pin Name	Pin Function
1	ENA	IC enable control input. Hi active. Internal pull-down resister (100k $\Omega$ ).
2, 20	NC	No internal connection.
3	VOUT4	Output voltage regulation node for LDO4.
4	PVD4	Power input for LDO4.
5	FB4	Feedback voltage input for LDO4
6	PVD2	Power input for Buck2.
7	LX2	Switch node of Buck2.
8	PGOOD	Buck1 to Buck 3, LDO4 and LSW PGOOD output node by open drain. Hi active.
9	FB2	Feedback voltage input for Buck2.
10	VOUT1S	HV buck output voltage for OVP detection. Input HV buck (CH1) output.
11	SEQ	Power sequence selection.
12	LX3	Switch node of Buck3.
13	PVD3	Power input for Buck3.
14	FB3	Feedback voltage input for Buck3.
15	SWO	Load switch output.
16	SWI	Load switch input.
17, 25 (Exposed Pad)	GND	IC power ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum thermal dissipation and current flow.
18	VIN	Power input for Buck1.
19	LX1	Switch node of Buck1.
21	FB1	Feedback voltage input for Buck1.
22	VDDA	IC internal analog power output 4.45V (typ.). Only $1\mu F$ and SCL/SDA pull up resister can be connected.
23	SDA	I <sup>2</sup> C data input/output.
24	SCL	I <sup>2</sup> C clock input.

### **Functional Block Diagram**



### Operation

The RT2070T is a highly-integrated solution for automotive systems, including a 1-CH HV step-down DC-DC converter, 2-CH LV step-down DC-DC converter and 1-CH LDO. The RT2070T application mechanism will be introduced in later sections.

The power-on and power-off sequences are detected in the SEQ pin. Additionally, users control the next power on/off sequence by setting  $I^2C$  registers from A01 to A12 when VDDA exists.

When the ENA pin is at Hi level, the PMIC follows the power-on sequence to turn on channels.

The IC turns on base and calibrates. Time is less than 500 $\mu s;$  during this time, the IC doesn't allow users to set  $I^2C$  data.

#### **Pre-Regulator**

This HV regulator is designed to handle input operation range of 4.5V to 15V. The regulator provides low voltage power to supply the internal control circuits and avoid connecting any load from VDDA pin. In noisy environments, a 1 $\mu$ F decoupling capacitor must be connected between VDDA and GND.

The I<sup>2</sup>C compatible interface remains fully functional if VIN and VDDA are present. If the VDDA is under the threshold voltage, all internal registers are reset to their default values.

#### **Over-Temperature Protection**

An Over-Temperature Protection (OTP) is featured in the device. The protection is triggered to force device shutdown when the junction temperature exceeds 160°C typically. If OTP is set to Hiccup once the junction temperature drops below the hysteresis 20°C typically, the device is re-enabled and automatically reinstated the power-on sequence.

#### Input Over-Voltage Protection

The device provides an input Over-Voltage Protection (OVP) once the input voltage exceeds 15.5V typically; the OVP function is started and all channels will be turned off after 5ms. If OVP is set to Hiccup, once the input voltage drops below the hysteresis 2V typically, the device is re-enabled and automatically reinstates the power-on sequence. This OVP feature can easily minimize the input overshoot.

#### ENA : IC Enable Pin

The ENA pin is a device enable input. Pulling the ENA pin to logic low that is typically less than the set threshold voltage 1.2V shuts the device down and it enters a low quiescent current state of about 20 $\mu$ A. The regulator starts switching again once the ENA pin voltage exceeds the threshold voltage of 2V. In addition, the ENA pin features an internal 100k $\Omega$  pull-low resistor.

#### Power Good (PGOOD) Control

The power good output is an open-drain output and needs to be connected to a voltage source with a pull-up  $10k\Omega$  resistor to avoid PGOOD floating. Each channel turns on according to power-on sequence. When the last channel reaches 90% of its target voltage, PMU (Power Management Unit) starts counting  $t_{PGOOD} = 5ms$  (Power Good Delay Time) then pulls PGOOD Hi until ENA is pulled low or any other protection happens.

### Absolute Maximum Ratings (Note 1)

Analog Base Input Voltage, VIN	-0.3V to 20V
Control Output Voltage, PGOOD	–0.3V to 6V
Control Input Voltage, ENA	–0.3V to 15V
HV Buck Power Switch (DC), LX1	–0.3V to 15V
LV Buck Input Voltage, PVD2/3	–0.3V to 6V
LV Buck Power Switch (DC), LX2, LX3	–0.3V to 6V
• LV Buck Power Switch (Spike Voltage < 200ns), LX2, LX3	–0.3V to 6V
Other Pins	-0.3V to 6V
<ul> <li>Power Dissipation, P<sub>D</sub> @ T<sub>A</sub> = 25°C</li> </ul>	
WQFN-24L 4x4	4.46W
Package Thermal Resistance (Note 2) (Note 3)	
WQFN-24L 4x4, $\theta_{JA}$	28°C/W
WQFN-24L 4x4, $\theta_{JC}$	7°C/W
Junction Temperature	150°C
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	$-65^\circ C$ to $150^\circ C$
ESD Susceptibility (Note 4)	
HBM (Human Body Model)	2kV

### Recommended Operating Conditions (Note 5)

Junction Temperature Range	–40°C to 150°C
Ambient Temperature Range	–40°C to 125°C

### **Electrical Characteristics**

(Note 8)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
VIN Operation Voltage Range			4.5		15	V
Quiescent Current	lq	$V_{IN} = 5V$ , Bucks and LDOs are ON with no load, HVBuck switching, LVBucks are in FCCM mode.	8	10	12	mA
Quescent Current	IQ_PSM	V <sub>IN</sub> = 5V, Bucks and LDOs are ON with no load, HVBuck non-switching, LVBucks are in PSM mode.	600	1000	1200	μΑ
Shutdown Current	I <sub>SHD</sub>	$V_{IN}$ = 5V, ENA = 0V, LDOs, Bucks are OFF.	2	7	20	μA
Over-Temperature Protection	OTP		150	160	170	°C
OTP Hysteresis (Note 6)	OTP_HYS		10	20	30	°C
VIN OVP (Hysteresis High)	OVP		14.5	15.5	16.5	V
VIN OVP Hysteresis (Gap) (Note 7)	OVP_HYS		1.5	2	2.5	V



Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit
VIN UVLO2	UVLO2		3.7	3.9	4.1	V
UVLO2 Hysteresis (Gap)	UVLO2_HYS		0.4	0.5	0.6	V
VDDA Voltage			4.2	4.5	4.8	V
Switching Frequency (CH1/CH2/CH3)	fsw		2 –10%	2	2 +10%	MHz
CH1 HV-Buck						
Input Voltage Range	Vin		4.5		15	V
Output Voltage Range	Vout		1.6		5	V
Feedback Voltage Accuracy	FB1		0.8 – 3%	0.8	0.8 + 3%	V
FB1 Under-Voltage Protection	FB1_UVP	FB1 = FB1 x 0.5 (50%)	0.3	0.4	0.5	V
Suggest Inductor	LHVBuck	Refer to Typical Application Circuit		4.7		μH
Ourse at Lineit	CL1	T <sub>A</sub> = 25℃	3 – 15%		3 + 15%	Â
	CL1_T	$-40^{\circ}C \leq T_A \leq 125^{\circ}C$	3 – 25%	3	3 + 25%	A
Load Regulation		$T_A = 25$ °C, V IN = 6V, V <sub>OUT</sub> = 3.3V, Load = 0mA to 2000mA Refer to Typical Operating Characteristics	-1		1	%
Line Regulation		$T_A = 25$ °C, V <sub>IN</sub> = 5V to 15V, V <sub>OUT</sub> = 3.3V, Load = 1000mA Refer to Typical Operating Characteristics	-1		1	%
P-MOSFET On-Resistance	R <sub>DS_ON_P</sub>	$V_{IN} = 5V, I_{LX1} = 800mA$	230	330	470	mΩ
N-MOSFET On-Resistance	Rds_on_n	$V_{IN} = 5V, I_{LX1} = 800mA$	100	150	250	mΩ
Soft-Start Time	t <sub>r1</sub>	$V_{OUT1} \ge 0.9 \text{ x } V_{Target},$ $I_{OUT} = 0 \text{mA}$	0.8	1.1	1.5	ms
Discharge Resistance		$V_{IN} = 5V$ , $V_{OUT} = 3.3V$	870	970	1070	Ω
Load Switch (LSW)						
Supply Voltage	V <sub>swi</sub>		2.7		5.5	V
MOSFET On-Resistance	R <sub>DS_ON</sub>	SWI = 3.3V, I <sub>OUT</sub> = 500mA	60	85	120	mΩ
	CLSW	T <sub>A</sub> = 25℃	750 – 15%	750	750 + 15%	~
	CLSW_T	$-40^{\circ}C \leq T_A \leq 125^{\circ}C$	750 - 20% 750 7		750 + 20%	mA
Under-Voltage Threshold	UVP_sw	V <sub>SWI</sub> – V <sub>SWO</sub>	0.5	0.7	0.9	V
Soft-Start Time	t <sub>r_sw</sub>	$V_{OUT} \ge 0.9 \text{ x } V_{Target},$ IOUT = 0mA	0.9	1.3	1.8	ms
Discharge Resistance		V <sub>OUT1</sub> = 3.3V, SWO = 3.3V	400	440	480	Ω

# **RT2070T**

Parameter	Parameter Symbol Test Conditions		Min	Тур	Max	Unit
Buck2 to Buck3		•				
Input Voltage Range	PVD2/PVD3		2.7		5.5	V
Output Voltage Range	Vout		1		3.6	V
Feedback Voltage Accuracy	FB2/3		0.8 – 3%	0.8	0.8 + 3%	V
Efficiency Peak	Eff	$V_{OUT} = 1.8V$ , $V_{IN} = 3.3V$ , $I_{LOAD} = 300mA$ Refer to Typical Operating Characteristics		92		%
Suggest Inductor	L <sub>Buck</sub>	Refer to Typical Application Circuit		2.2		μH
Current Limit	CL2/3	T <sub>A</sub> = 25℃	1300 - 15%	1300	1300 + 15%	٣٨
	CL2/3_T	$-40^{\circ}C \leq T_A \leq 125^{\circ}C$	1300 - 25%	1300	1300 + 25%	IIIA
FB2/3 Under-Voltage Protection	UVP2/3	FB2/3 = FB2/3 x 0.5 (50%)		0.4		V
Load Regulation		$T_A = 25$ °C, PVD2/3 = 3.3V, V <sub>OUT</sub> = 1.2V, Load = 0mA to 1000mA Refer to Typical Operating Characteristics	-1		1	%
Line Regulation		$T_A = 25$ °C, PVD2/3 = 3V to 5.5V, V <sub>OUT</sub> = 1.2V, Load = 1000mA Refer to Typical Operating Characteristics	-1		1	%
P-MOSFET On-Resistance	Rds_on_p	PVD2/3 = 3.3V	180	270	370	mΩ
N-MOSFET On-Resistance	Rds_on_n	PVD2/3 = 3.3V	100	175	250	mΩ
Soft-Start Time	oft-Start Time $t_{r_{2/3}}$ $V_{OUT_{2/3}} \ge 0.9 \text{ x } V_{Target}, I_{OUT} = 0 \text{ mA}$		0.8	1	1.5	ms
Discharge Resistance		PVD2 = 3.3V, V <sub>OUT</sub> = 1.2V	5	6	7	0
Discharge Resistance		PVD3 = 3.3V, V <sub>OUT</sub> = 1.8V	6	7	8	22
CH4 LDO	_					
Input Voltage for PVD4	PVD4		2.7		5.5	V
Output Voltage Range	Vout		1		3.6	V
Feedback Voltage Accuracy	FB4		0.8 – 3%	0.8	0.8 + 3%	V
Current Limit	CL4	T <sub>A</sub> = 25℃	750 – 15%	750	750 + 15%	m۸
	CL4_T	$-40^{\circ}C \leq T_A \leq 125^{\circ}C$	750 – 30%	750	750 + 35%	
Dropout Voltage (PVD4 – V <sub>OUT4</sub> )	Vdrop	I <sub>OUT</sub> = 150mA, PVD4 = V <sub>OUT4</sub> - 0.1V	0.01		0.15	V



Parame	ter	Symbol	Test Conditions	Min	Тур	Max	Unit
Line Regulation		LiR	$T_A = 25$ °C, PVD4 = 3V to 5V, $V_{OUT4} = 2.7$ V, Load = 100mA Refer to Typical Operating Characteristics			0.5	%
Load Regulation		LoR	$T_A = 25$ °C, PVD4 = 3.3V, Load 10mA to 500mA Refer to Typical Operating Characteristics		0.1	1	%
FB4 Under-Volta Protection	ge	FB4_UVP	FB4 = 0.8V x 0.4 (40%)	0.2	0.3	0.4	V
PSRR			Feq = 1kHz, $I_{OUT}$ = 10mA, $V_{OUT}$ = 2.7V Refer to Typical Operating Characteristics		60		dB
Soft-Start Time		tr4	$V_{OUT4} \ge 0.9 \text{ x } V_{Target}, I_{OUT} = 0 \text{mA}$	0.6	1	1.5	ms
Discharge Resist	ance		PVD4 = 3.3V, V <sub>OUT</sub> = 2.7V	380	450	520	Ω
Power Good			·				
Power Good Pull Voltage	-Down	PGOOD	PGOOD current equal to 5mA		200		mV
Power Good Delay Time		t <sub>PGOOD</sub>			5		ms
Control							
ENA Input	Logic-High			2			V
Voltage	Logic-Low					0.5	v
ENA Pull High Cu	urrent	IPULL	$V_{IN} = 5V$ , Temperature = $-40^{\circ}C$ to $125^{\circ}C$	20	37	55	μΑ

- Note 1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2.  $\theta_{JA}$  is measured under natural convection (still air) at  $T_A = 25^{\circ}C$  with the component mounted on a high effectivethermal-conductivity four-layer test board on a JEDEC 51-7 thermal measurement standard.  $\theta_{JC}$  is measured at the exposed pad of the package.
- Note 3. The junction temperature(T<sub>J</sub> in °C) is calculated from the ambient temperature (T<sub>A</sub> in °C) and power dissipation (P<sub>D</sub> in watts) according to the formula : T<sub>J</sub> = T<sub>A</sub> + (P<sub>D</sub> x  $\theta_{JA}$ ) where  $\theta_{JA}$  (in °C/W) in the package thermal impedance. Another, P<sub>IN</sub> - P<sub>O</sub> = P<sub>D</sub> and P<sub>O</sub> =  $\eta x P_{IN} \rightarrow P_D = (1 / \eta - 1) x P_O$  where P<sub>IN</sub> is the total input power and Po is the total output power.
- Note 4. Devices are ESD sensitive. Handling precaution is recommended.
- Note 5. The device is not guaranteed to function outside its operating conditions.
- Note 6. When OTP is set to Hiccup by I<sup>2</sup>C.
- Note 7. When VIN OVP is set to Hiccup by  $I^2C$
- Note 8. Limits apply to the recommended  $V_{IN} = 4.5V$  to 15V,  $T_A = -40^{\circ}C$  to 125°C, unless otherwise noted. Minimum and maximum limits are verified through test, design, or statistical correlation. Typical values represent the most likely parametric norm at  $T_A = 25^{\circ}C$ , and are provided for reference purposes only.

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### **Typical Application Circuit**



If there is any CHx is not used that external components still must be existed and keep original application circuit. If LSW isn't used, user can remove C2, C3 and C4, but the SWI pin must connect to VOUT1 and floating the SWO pin.



Reference	Q'ty	P/N	Description	Manufacturer
C1	1	GCM188R61A105KA37D	1µF/10V/X5R	MURATA
C2, C3, C4, C102, C202, C203, C302, C303	8	GCM21BR71A106KE22L	10μF/10V/X7R	MURATA
C101	1	GRM31CR71E475KA40	4.7μF/25V/X7S	MURATA
C201, C301, C401	3	GCM21BC71A475KA73L	4.7μF/10V/X7S	MURATA
C402	1	GCM21BR71A225KA01	2.2μF/10V/X7R	MURATA
C204	1	GCM1885C1H121JA16#	120pF/50V/C0G	MURATA
C304	1	GCM1885C1H221JA16D	220pF/50V/C0G	MURATA
C404	1	GCM1885C1H470JA16D	470pF/50V/C0G	MURATA
L101	1	LQH5BPB4R7NT0L	4.7μH	MURATA
L201, L301	2	LQH32PB2R2NN0L	2.2µH	MURATA
R101	1	RM06FTN1502	15k/1%	TA-I
R102	1	RM06FTN4751	4.75k/1%	TA-I
R203	1	RM06FTN2702	27k/1%	TA-I
R204	1	RM06FTN2152	21.5k/1%	TA-I
R303	1	RM06FTN1402	14k/1%	TA-I
R304	1	RM06FTN2802	28k/1%	TA-I
R403	1	RM06FTN2212	22.1k/1%	TA-I
R404	1	RM06FTN9311	9.31k/1%	TA-I

#### Table 1. Suggested Components for Typical Application Circuit

### **Typical Operating Characteristics**





Output Current (mA)





CH1 HV Buck Output Voltage vs. Output Current















3.36 3.35 Output Voltage (V) 3.34 3.33 3.32 IOUT = 0mAlouт = 500mA IOUT = 1000mA 3.31 louт = 1500mA IOUT = 2000mA  $L = 4.7 \mu H$ ,  $C_{OUT} = 10 \mu F \times 2$ 3.30 5 6 7 8 9 10 11 12 13 14 15

CH1 HV Buck Output Voltage vs. Input Voltage



CH3 Buck Output Voltage vs. Input Voltage



CH4 LDO Dropout Voltage vs. Load Current



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### **Applications Information**

The RT2070T is a highly integrated automotive system Power Management IC that contains 3-CH switching DC-DC converters and one generic LDO and one load switch.

#### CH1 : HV Step-Down DC-DC Converter

CH1 is a HV step-down converter for LV DC-DC converter power. The current-mode PWM converter with integrated internal MOSFETs and compensation network operates at fixed frequency. The output voltage of CH1 is set by external feedback resistors, as expressed in the following equation :

VOUT1 = (1 + R101 / R102) x V<sub>FB1</sub>

Where  $V_{\text{FB1}}$  is 0.8V typically and suggested value for R101 is 10k to 500k.

#### CH2 : Synchronous Step-Down DC-DC Converter

CH2 is a synchronous step-down converter for I/F power and it operates with typically 2MHz fixed frequency Pulse Width Modulation (PWM) at moderate to heavy load currents. At light load currents, the converter can automatically enter Power Save Mode and operates in PFM mode which can be set by I<sup>2</sup>C interface.

The converter output voltage is externally adjustable using a resistor divider at FB2.

The output voltage of CH2 is set by external feedback resistors, as expressed in the following equation :

VOUT2 = (1 + R203 / R204) x V<sub>FB2</sub>

Where  $V_{\text{FB2}}$  is 0.8V typically and suggested value for R203 is 10k to 600k.

#### CH3 : Synchronous Step-Down DC-DC Converter

CH3 is suitable for logic power. The converter with integrated internal MOSFETs and compensation network operates at synchronous PSM or fixed frequency PWM current mode which can be set by the I<sup>2</sup>C interface. The output voltage of CH3 is set by external feedback resistors, as expressed in the following equation :

VOUT3 = (1 + R303 / R304) x V<sub>FB3</sub>

Where  $V_{\text{FB3}}$  is 0.8V typically and suggested value for R303 is 10k to 600k.

For CH2 and CH3, to improve control performance using a feedforward capacitor in parallel to R203 or R303 is recommended, the value for the feedforward capacitor can be calculated using below formula :

For CH2, 
$$C_{FF} = \frac{3.16\mu s}{R203}$$
  
For CH3,  $C_{FF} = \frac{3.16\mu s}{R303}$ 

#### CH4 : Generic LDO

CH4 is a low-dropout (LDO) voltage regulator which offers benefits of high input voltage and low-dropout voltage for sensor power. The output voltage of CH4 is set by external feedback resistors, as expressed in the following equation :

VOUT4 = (1 + R403 / R404) x V<sub>FB4</sub>

Where  $V_{\text{FB4}}$  is 0.8V typically and suggested value for R403 is 5k to 500k.

To improve control performance using a feedforward capacitor in parallel to R403 is recommended, the value for the feedforward capacitor can be calculated using below formula :

 $C_{FF} = \frac{10.4 \mu s}{R403}$ 

#### Load Switch : Load Switch

The load switch for core power is equipped with soft-start control and current limit function.

If LSW isn't used, user can remove C2, C3 and C4, but the SWI pin must connect to VOUT1 and floating the SWO pin.

#### Input and Output Capacitors Selection

The RT2070T is designed to work with low ESR ceramic capacitors. The *effective* value of these capacitors is defined as the actual capacitance under voltage bias and temperature. All ceramic capacitors have a large voltage coefficient, in addition to normal tolerances and temperature coefficients. Under D.C. bias, the capacitance value drops considerably. Larger case sizes or higher voltage capacitors are better in this regard. To help mitigate these effects, multiple small capacitors can be used in parallel to bring the minimum effective capacitance up to the desired value.

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The input capacitance,  $C_{IN}$ , is needed to filter the trapezoidal current at the source of the top MOSFET. A low ESR input capacitor with larger ripple current rating should be used for the maximum RMS current. RMS current is given by :

$$I_{RMS} = I_{OUT}(MAX) \frac{V_{OUT}}{V_{IN}} \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

This formula has a maximum at  $V_{IN} = 2V_{OUT}$ , where  $I_{RMS} =$ IOUT / 2. This simple worst case condition is commonly used for design because even significant deviations do not offer much relief. Note that ripple current ratings from capacitor manufacturers are often based on only 2000 hours of life, which makes it advisable to either further derate the capacitor or choose a capacitor rated at a higher temperature than required. Several capacitors may also be placed in parallel to meet size or height requirements in the design. The selection of COUT is determined by the effective series resistance (ESR) that is required to minimize voltage ripple, load step transients, and the amount of bulk capacitance that is necessary to ensure that the control loop is stable. Loop stability can be examined by viewing the load transient response as described in a later section. The output ripple,  $\Delta V_{OUT}$ , is determined by :

 $\Delta V_{OUT} \le \Delta I_L \left[ ESR + \frac{1}{8 f C_{OUT}} \right]$ 

The output ripple is highest at maximum input voltage since DIL increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirements. Dry tantalum, special polymer, aluminum electrolytic and ceramic capacitors are all available in surface mount packages. Special polymer capacitors offer very low ESR but have lower capacitance density than other types. Tantalum capacitors have the highest capacitance density but it is important to only use types that have been surge tested for use in switching power supplies. Aluminum electrolytic capacitors have significantly higher ESR but can be used in cost-sensitive applications provided that consideration is given to ripple current ratings and long-term reliability. Ceramic capacitors have excellent low ESR characteristics but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing.

Application	C <sub>OUT</sub> ESR Range
CH1 C <sub>OUT</sub>	5 to 15m $\Omega$
CH2 C <sub>OUT</sub>	5 to 15m $\Omega$
CH3 C <sub>OUT</sub>	5 to 15m $\Omega$
CH4 C <sub>OUT</sub>	5 to $10m\Omega$

0		<b>D</b>	- 1		
Suggestion	ESK	Range	ΟΤ	output	capacitor

#### Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. However, care must be taken when these capacitors are used at the input and output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input,  $V_{IN}$ . At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at VIN large enough to damage the part. Table 1 shows the nominal values of input/output capacitance recommenced for the RT2070T.

#### **Inductor Selection**

For a given input and output voltage, the inductor value and operating frequency determine the ripple current. The ripple current  $\Delta I_L$  increases with higher VIN and decreases with higher inductance :

$$\Delta I_{L} = \left[\frac{V_{OUT}}{f_{OSC} \times L}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN}}\right]$$

Having a lower ripple current reduces the ESR losses in the output capacitors and the output voltage ripple. Highest efficiency operation is achieved at low frequency with small ripple current. This, however, requires a large inductor. A reasonable starting point for selecting the ripple current is  $\Delta I_L = 0.4$  (I<sub>MAX</sub>). The largest ripple current occurs at the

highest  $V_{IN}$ . To guarantee that the ripple current stays below a specified maximum, the inductor value should be chosen according to the following equation :

I –	Vout		- 1_	Vout	]
L –	$fosc \times \Delta I_{L(MAX)}$		-	VIN(MAX)	

#### **Inductor Core Selection**

Once the value for L is known, the type of inductor must be selected. High efficiency converters generally cannot afford the core loss found in low cost powdered iron cores, forcing the use of more expensive ferrite or permalloy cores. Actual core loss is independent of core size for a fixed inductor value but it is very dependent on the inductance selected. As the inductance increases, core losses decrease. However, increased inductance requires more turns of wire and therefore copper losses will increase.

Ferrite designs have very low core losses and are preferred at high switching frequencies, so design goals can concentrate on copper loss and preventing saturation.

Ferrite core material saturates "hard", which means that inductance collapses abruptly when the peak design current is exceeded.

This results in an abrupt increase in inductor ripple current and consequent output voltage ripple.

Do not allow the core to saturate!

Different core materials and shapes will change the size/ current and price/current relationship of an inductor. Toroid or shielded pot cores in ferrite or permalloy materials are small and don't radiate energy but generally cost more than powdered iron core inductors with similar characteristics. The choice of which style inductor to use mainly depend on the price vs. size requirements and any radiated field/EMI requirements.

#### **Power On/Off Control**

The register value will be recovered to default value as VIN plug in. In normal operation, users can set the power on/ off relative setting by I<sup>2</sup>C for next ENA power on. The RT2070T support 6 sets power on/off sequence selected by the SEQ pin. The sequence detection operation only work as VIN plug in. The RT2070T includes 6 sets power on/off sequence and the default value is decided by factory trim.

In the RT2070T, users can plan the next power on/off sequence by setting register A01/A02. The register value means the power on location, and "000" means this channel is power off. The RT2070T doesn't allow missing power on code or discrete code occurs.

	SEQ0 to SEQ5							
	Output Voltage Setting	Soft-Start End Delay Time (A01.Bit [7:6])	Discharge Finish Delay Time (A02.Bit [7:6])					
	SEQX_LSW [2:0]							
LSVV	[001]							
D I O	SEQX_Buk2 [2:0]							
DUCKZ	[010]	[00]	[00]					
Duale?	SEQX_Buk3 [2:0]	[00]	[00]					
	[011]							
	SEQX_LDO [2:0]							
	[100]							

#### Note :

The default value will be decided in factory trim.

Define :

[000] means channel always turn off.

[001] means firstly turn on channel.

-----

[100] means the finally turn on channel.

Example :

In above setting, the power on sequence is as below : LSW (001)  $\rightarrow$  Buck2 (010)  $\rightarrow$  Buck3 (011)  $\rightarrow$  LDO4 (100).

#### Normally Power ON/OFF Sequence

In the RT2070T, the power on sequence of the channels are decided by SEQ setting. The off sequence will follow firston-last-off rule to turn off channels.



**Note :** ON\_td and OFF\_td time control by Register ON\_td <1:0> and OFF\_td <1:0>, default setting <00> = 0ms, and  $t_{PGOOD} = 5ms$ .

Figure 1. Sequence Example : CH1  $\rightarrow$  CH2  $\rightarrow$  CH4  $\rightarrow$  LSW  $\rightarrow$  CH3

#### Abnormal Off

When the abnormal event occurs, all channels turns off immediately.

If users want to turn on again, users must pull ENA low to reset state then pull high to turn on again.



Note : ON\_td and OFF\_td time control by Register ON\_td <1:0> and OFF\_td <1:0> , default setting <00> = 0ms, and  $t_{PGOOD} = 5ms$ .



When output channel take time to discharge over 64ms and ENA keep low level, all channels turn off at 64ms after starting Power Off Sequence.



Figure 3. Sequence Example : Power ON (CH1 $\rightarrow$  CH2 $\rightarrow$  CH3 $\rightarrow$  CH4 $\rightarrow$  LSW), Power OFF (LSW $\rightarrow$ CH4 $\rightarrow$  CH3  $\rightarrow$  CH2 $\rightarrow$ CH1)

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When output channel take time to discharge over 64ms and ENA goes high level at 64ms after starting Power Off Sequence, the RT2070T re-start immediately.



Figure 4. Sequence Example : Power ON (CH1→ CH2→ CH3→ CH4→ LSW), Power OFF (LSW → CH4 → CH3  $\rightarrow$  CH2  $\rightarrow$  CH1)

When output channel take time to discharge over 64ms and ENA keep high level at 64ms after starting Power Off Sequence, the RT2070T re-start immediately.



Figure 5. Sequence Example : Power ON (CH1→ CH2→ CH3→ CH4→ LSW), Power OFF (LSW → CH4 → CH3  $\rightarrow$  CH2  $\rightarrow$  CH1)



#### PMU On/Off Sequence Setting by SEQ

The SEQ pull-down resistance is used to define power on/off sequence (SEQ1 to SEQ5).

The RT2070T will do sequence detection as VIN plug in. Enable sequence will be executed when detection phase finish. If users don't change the sequence setting by I<sup>2</sup>C in register A01 to A12, the IC will follow default value to turn on IC set by factory trim. If there is any CHx is not used that external components still must be existed and keep original application circuit.



SEQ	RSEQ Range	Typical R <sub>SEQ</sub>
SEQ0	Short to VDDA	
SEQ1	$64k\Omega > R_{SEQ} > 30k\Omega$	47kΩ
SEQ2	$16k\Omega > R_{SEQ} > 6.8k\Omega$	10kΩ
SEQ3	$3.9 \text{k}\Omega > \text{R}_{\text{SEQ}} > 1.6 \text{k}\Omega$	2.4kΩ
SEQ4	Short to GND	
SEQ5	$200 k\Omega > R_{SEQ} > 110 k\Omega$	160kΩ

Users can plan the combination of six sequences (SEQ0 to SEQ5).

SEQ0	CH1	CH2	LSW	CH3	CH4
SEQ1	CH1	LSW	CH4	СНЗ	CH2
SEQ2	CH1	CH4	СНЗ	CH2	LSW
SEQ3	CH1	CH2	CH3	LSW	CH4
SEQ4	CH2	CH1	СНЗ	CH4	LSW
SEQ5	CH1	LSW	CH2	CH4	CH3

#### **VIN UVLO2 Operation**

If VIN is smaller than 3.9V, all channels will be turned off after 32µs.

Next, V<sub>IN</sub> is larger than 4.4V, the system will be sequence turn on by setting.

#### Max Load of Every Channel

Purpose	RT2070T	Peak Current Limit	Max Loading (I <sub>OUT</sub> )*	Condition (V <sub>IN</sub> $\rightarrow$ V <sub>OUT</sub> )
HV to LV	CH1_HV Buck	3000mA	2000mA	5V  ightarrow 3.3V
V <sub>I/O</sub>	CH2_LV Buck	1300mA	900mA	3.3V  ightarrow 1.8V
V <sub>CORE</sub>	CH3_LV Buck	1300mA	1000mA	3.3V  ightarrow 1.2V
VSENSOR	CH4_LDO	750mA	500mA	3.3V  ightarrow 2.7V
Load SW	LSW	750mA	500mA	$3.3V \rightarrow 3.3V$

\* Buck converter VIN/VOUT levels will affect the max loading

Higher max loading current

Higher step-down ratio (VIN/VOUT) results in shorter switch on-time (ton), hence lower peak switch current.

Lower max loading current

Lower step down ratio (VIN closer to VOUT) results a lower differential inductor voltage, so the slope of the inductor current during the ramp-up period is reduced.





**Note :** 0.5V is hysteresis voltage.

Figure 6. UVLO2 Diagram

#### **Protection Act**

	UVLO2
Protection Action	Hiccup
Vth_R(V)	4.4
Vth_F(V)	3.9
Power On Confirm	YES
Detect Power Pin	VIN

\*Hiccup : Recover automatically.



#### Flow Chart Power ON/OFF Operation



#### **Flow Chart of Protection**



### I<sup>2</sup>C Interface

Driven by Master

The RT2070T I<sup>2</sup>C interface bus power must be supplied by VDDA or equal potential node. If I<sup>2</sup>C interface isn't used, SDA and SCL must be connected to GND. The RT2070T

 $I^2C$  slave address = 0110100 (7bits).  $I^2C$  interface supports fast mode (bit rate up to 400kb/s). The write or read bit stream (N  $\geq$  1) is shown below :



S Start

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
I <sup>2</sup> C Interface Electrical Charac	teristics					
Pull Up Voltage Range			1.8		VDDA	V
SCLK Clock Rate	f <sub>SCL</sub>				400	kHz
Hold Time (Repeated) START Condition. After this period, the first clock pulse is generated	thd;sta		0.6			μs
LOW Period of the SCL Clock	tLOW		1.3			μs
HIGH Period of the SCL Clock	tнigн		0.6			μs
Set-Up Time for a Repeated START Condition	tsu;sta		0.6			μs
Data Hold Time	thd;dat		0		0.9	μs
Data Set-Up Time	tsu;dat		100			ns
Set-Up Time for STOP Condition	tsu;sto		0.6			μs
Bus Free Time Between a STOP and START Condition	tBUF		1.3			μs
Rise Time of Both SDA and SCL Signals	t <sub>R</sub>		20		300	ns
Fall Time of Both SDA and SCL Signals	tF		20		300	ns
SDA and SCL Output Low Sink Current	I <sub>OL</sub>	SDA or SCL voltage = 0.4V	2			mA

#### I<sup>2</sup>C Waveform Information



#### I<sup>2</sup>C Register Table

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				Buck Fur	nction Trim	1		
A00	0x00	Meaning	Reserved	FPWM3	FPWM2	EnDis_ LDO	EnDis_ buck3	EnDis_ buck2	Reserved	Reserved
		Default	0	1	1	1	1	1	0	0
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define the	e Buck3 s	witching op	peration m	ode			
	FPWM	3	0 : Autom 1 : Force	atic PWM PWM	/PSM swit	ching ope	ration			
			Define the	e Buck2 s	witching o	peration m	ode			
	FPWM	2	0 : Autom 1 : Force	atic PWM PWM	/PSM swit	ching ope	ration			
			LDO pow	er off disc	harge ena	ble contro	I			
	EnDis_LI	00	0 : Won't 1 : Discha	discharge arge when	when LDO LDO pow	D power of er off	ff			
			Buck3 po	wer off dis	scharge en	able conti	rol			
	EnDis_bu	ck3	0 : Won't 1 : Discha	discharge arge when	when Buc Buck3 po	k3 power wer off	off			
			Buck2 po	wer off dis	scharge en	able conti	rol			
	EnDis_bu	ck2	0 : Won't 1 : Discha	discharge arge when	when Buc Buck2 po	k2 power wer off	off			



Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ	) Trim			
4.01	0.01	Meaning	ON_td	<1:0>	SEC	0_Buk2 <	2:0>	SEC	Q0_LSW <	2:0>
AUT	0x01	Default	0	0	0	0	1	0	1	0
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define the	e interval b	between so	oft-start fin	ish and the	e next chai	nnel enabl	ed
	ON_td <1	:0>	11 : 2ms 10 : 1ms 01 : 0.5m 00 : 0ms	S						
			Define Bu (Note : ev	uck2 powe /ery chann	r on seque lel can't ch	nce in SE oose the s	Q0 ame code	except <0	)00> in SE	Q0)
SE	Q0_Buck2	2 <2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn of third turn of second tur first turn o able	n on rn on n					
			Define LS (Note : ev	SW power very chann	on sequen lel can't ch	ce in SEQ oose the s	0 ame code	except <0	)00> in SE	Q0)
SE	EQ0_LSW	<2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn o third turn c second tur first turn o able	n on rn on n					

# **RT2070T**

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ0	Trim			
402	0202	Meaning	OFF_te	d <1:0>	SEC	20_LDO <	2:0>	SEC	0_Buk3 <	2:0>
AUZ	0x02	Default	0	0	1	0	0	0	1	1
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define the	interval be	tween shu	ıt-down Ol	K and the	next chani	nel disable	эd
	OFF_td <′	1:0>	11 : 2ms 10 : 1ms 01 : 0.5ms 00 : 0ms	3						
			Define Bu (Note : ev	ck3 power o ery channel	on sequen   can't cho	ce in SEC ose the sa	0 Ime code (	except <00	00> in SE0	Q0)
SE	Q0_Buck3	3 <2:0>	100 : the l 011 : the t 010 : the s 001 : the f 000 : disa	ast turn on hird turn on second turn irst turn on ole	on					
			Define LD (Note : ev	O power or ery channel	n sequence can't cho	e in SEQ0 ose the sa	ime code (	except <00	00> in SE0	Q0)
SE	EQ0_LDO	<2:0>	100 : the l 011 : the t 010 : the s 001 : the f 000 : disal	ast turn on hird turn on second turn irst turn on ole	on					

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ1	Trim			
A02	0×03	Meaning	Reserved	Reserved	SEC	1_Buk2 <	2:0>	SEC	21_LSW <	2:0>
A03	0x03	Default	0	0	1	0	0	0	0	1
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define Bu (Note : eve	ck2 power o ery channel	on sequen can't cho	ce in SEQ ose the sa	1 me code e	except <00	0> in SEC	Q1)
SE	Q1_Buck2	2 <2:0>	100 : the la 011 : the the solution of the sol	ast turn on hird turn on second turn irst turn on ole	on					
			Define LS (Note : eve	W power or ery channel	n sequenco can't choo	e in SEQ1 ose the sa	me code e	except <00	)0> in SEC	Q1)
SE	EQ1_LSW	<2:0>	100 : the l 011 : the t 010 : the s 001 : the f 000 : disal	ast turn on hird turn on second turn irst turn on ole	on					



Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ1	Trim			
104	0x04	Meaning	Reserved	Reserved	SEC	Q1_LDO <	2:0>	SEC	)1_Buk3 <	2:0>
A04	0x04	Default	1	0	0	1	0	0	1	1
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define LE (Note : ev	OO power or very channe	n sequenc I can't cho	e in SEQ bose the s	l ame code	except <0	00> in SE	Q1)
S	EQ1_LDO	<2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ıble	ו ו on					
			Define Bu (Note : ev	uck3 power very channe	on sequer I can't cho	nce in SEC	Q1 ame code	except <0	00> in SE	Q1)
SE	Q1_Buck	3 <2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ıble	ו ו on					

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ2	Trim			
A.05	0.405	Meaning	Reserved	Reserved	SEC	)2_Buk2 <	2:0>	SEC	2_LSW <	2:0>
AUS	0x05	Default	0	0	0	1	1	1	0	0
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
			Define Bu (Note : ev	ick2 power ery channe	on sequer I can't cho	nce in SEC	Q2 ame code	except <0	00> in SE	Q2)
SE	Q2_Buck2	2 <2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ıble	ו ס on					
			Define LS (Note : ev	SW power o very channe	n sequeno I can't cho	ce in SEQ2	2 ame code	except <0	00> in SE	Q2)
SI	EQ2_LSW	<2:0>	100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ıble	ו ו on					

|--|

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ2	Trim			
100	0,000	Meaning	Reserved	Reserved	SEC	22_LDO <	2:0>	SEQ2_Buk3 <2:0		2:0>
AUG	0000	Default	0	0	0	0	1	0	1	0
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
Define LDO power on sequence in SEQ2 (Note : every channel can't choose the same code except <000> in SEQ2							Q2)			
SE	EQ2_LDO	<2:0>	100 : the la 011 : the tl 010 : the s 001 : the f 000 : disal	ast turn on hird turn on second turn irst turn on ble	on					
			Define Bue (Note : eve	ck3 power o ery channel	on sequen can't choo	ce in SEQ ose the sa	2 me code e	except <00	)0> in SEC	J2)
SEQ2_Buck3 <2:0>			100 : the la 011 : the the solution of the sol	ast turn on hird turn on second turn irst turn on ble	on					

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
		Function				SEQ3	Frim				
407	0,07	Meaning	Reserved	Reserved	SEC	}3_Buk2 <	2:0>	SEQ	3_LSW <2	_LSW <2:0>	
AUT	0x07	Default	0	0	0	0	1	0	1	1	
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
			Define Buck2 power on sequence in SEQ3 (Note : every channel can't choose the same code except <000> in SEQ3)								
SE	Q3_Buck2	2 <2:0>	100 : the la 011 : the tl 010 : the s 001 : the fi 000 : disal	ast turn on hird turn on econd turn rst turn on ble	on						
			Define LS (Note : eve	N power on ery channel	sequence can't choo	e in SEQ3 ose the sa	me code e	except <00	0> in SEC	<b>)</b> 3)	
SEQ3_LSW <2:0>			100 : the la 011 : the the 010 : the s 001 : the fi 000 : disat	ast turn on hird turn on econd turn rst turn on ble	on						



Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
		Function				SEQ3	Trim				
100	0,00	Meaning	Reserved	Reserved	SEC	Q3_LDO <	2:0>	SEQ3_Buk3 <2:0>			
AUO	0,000	Default	0	0	1	0	0	0	1	0	
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
Define LDO power on sequence in SEQ3 (Note : every channel can't choose the same code except <000> in SEQ3)						Q3)					
SEQ3_LDO <2:0>			100 : the 011 : the 010 : the 001 : the 000 : disa	100 : the last turn on 011 : the third turn on 010 : the second turn on 001 : the first turn on 000 : disable							
			Define Bu (Note : ev	ick3 power ery channe	on sequer I can't cho	nce in SEC	23 ame code	except <0	00> in SE	Q3)	
SEQ3_Buck3 <2:0>		100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ble	ı ı on							

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0			
		Function		SEQ4 Trim									
100	0×00	Meaning	Reserved	Reserved	SEC	)4_Buk2 <	2:0>	SEC	04_LSW <	2:0>			
AU9	0x09	Default	0	0	0	0	1	1	0	0			
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W			
			Define Buck2 power on sequence in SEQ4 (Note : every channel can't choose the same code except <000> in SEQ4)										
SEQ4_Buck2 <2:0>			100 : the last turn on 011 : the third turn on 010 : the second turn on 001 : the first turn on 000 : disable										
			Define LSW power on sequence in SEQ4 (Note : every channel can't choose the same code except <000> in SEQ4)										
SEQ4_LSW <2:0>		100 : the 011 : the 010 : the 001 : the 000 : disa	last turn on third turn or second turr first turn on ıble	า i on									

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
		Function				SEQ4	Trim				
A 1 0	0.00	Meaning	Reserved	Reserved	SEC	Q4_LDO <	2:0>	SEQ4_Buk3 <2:0>			
AIU	UXUA	Default	0	0	0	1	1	0	1	0	
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
			Define LDO power on sequence in SEQ4 (Note : every channel can't choose the same code except <000> in SEQ4)								
SEQ4_LDO <2:0>			100 : the last turn on 011 : the third turn on 010 : the second turn on 001 : the first turn on 000 : disable								
			Define Bu (Note : ev	ck3 power o ery channel	on sequen   can't cho	ce in SEC ose the sa	4 Ime code (	except <00	00> in SE0	Q4)	
SEQ4_Buck3 <2:0>		100 : the l 011 : the t 010 : the s 001 : the f 000 : disa	ast turn on hird turn on second turn irst turn on ble	on							

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0		
		Function				SEQ5 Trim						
A 1 1		Meaning	Reserved	Reserved	SEC	§5_Buk2 <	2:0>	SEC	SEQ5_LSW <2:0>			
AII	UXUB	Default	0	0	0	1	0	0	0	1		
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W		
			Define Buck2 power on sequence in SEQ5 (Note : every channel can't choose the same code except <000> in SEQ5)									
SEQ5_Buck2 <2:0>			100 : the last turn on 011 : the third turn on 010 : the second turn on 001 : the first turn on 000 : disable									
			Define LSW power on sequence in SEQ5 (Note : every channel can't choose the same code except <000> in SEQ5)									
SEQ5_LSW <2:0>		100 : the l 011 : the t 010 : the s 001 : the f 000 : disa	ast turn on hird turn on second turn irst turn on ble	on								



Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
		Function				SEQ	5 Trim			
A10	0,400	Meaning	Reserved	Reserved	SEC	25_LDO <	2:0>	SEQ5_Buk3 <2:0>		
AIZ	UXUC	Default	0	0	0	1	1	1	0	0
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W
Define LDO power on sequence in SEQ5 (Note : every channel can't choose the same code exc						e except <0	00> in SE(	Q5)		
SI	EQ5_LDO	<2:0>	100 : the I 011 : the t 010 : the s 001 : the f 000 : disa	ast turn on hird turn or second turn ïrst turn on ble	i i on					
			Define Bu (Note : ev	ck3 power ery channe	on sequei I can't cho	nce in SE bose the s	Q5 ame code	e except <0	00> in SE(	Q5)
SE	Q5_Buck	3 <2:0>	100 : the I 011 : the t 010 : the s 001 : the f 000 : disa	ast turn on hird turn or second turn ïrst turn on ble	i I on					

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0		
		Function			OTP/O	VP Functic	on Level Tri	im				
A13	0x0D	Meaning	OTP_ TypeSel	Reserved	Reserved	Reserved	Reserved	VINOVP_ TypeSel	VIN TDSE	OVP_ L <1:0>		
		Default	1	1	0	0	1	0	1	0		
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W		
			Define OTP protection operation mode.									
	OTP_TypeSel		0 : Hiccup protection 1 : Latch-off protection									
			Define OVP protection operation mode.									
VI	INOVP_Ty	rpeSel	0 : Hiccup protection 1 : Latch-off protection									
			Define OVP deglitch time									
VINOVP_TDSEL <1:0>		11 : 10ms 10 : 5ms 01 : 1ms 00 : 0ms										

# **RT2070T**

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
		Function		•	Bu	ck2/3 Perfo	ormance T	rim			
A14	0x0E	Meaning	Buck3N <1	ИР_Cur :0>	Buck3D	Buck3Drv <1:0>		Buck2MP_Cur <1:0>		rv <1:0>	
A14 Buck: Buck		Default	1	0	1	0	1	0	1	0	
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
			Define th	e Buck3 m	iinimum pe	ak current	level				
Buc	ck3MP_Cu	ır <1:0>	11 : Minir 10 : Minir 01 : Minir 00 : Minir	<ul> <li>11 : Minimum Peak Current Level = 210mA</li> <li>10 : Minimum Peak Current Level = 170mA</li> <li>01 : Minimum Peak Current Level = 110mA</li> <li>00 : Minimum Peak Current Level = 70mA</li> </ul>							
			Define Bu	uck3 driver	r ability						
В	8uck3Drv <	<1:0>	11 : stronger 10 : middle 01 : weaker 00 : weakest								
			Define the Buck2 minimum peak current level								
Buc	ck2MP_Cu	ır <1:0>	<ul> <li>11 : Minimum Peak Current Level = 210mA</li> <li>10 : Minimum Peak Current Level = 170mA</li> <li>01 : Minimum Peak Current Level = 110mA</li> <li>00 : Minimum Peak Current Level = 70mA</li> </ul>								
			Define Bu	uck2 driver	r ability						
В	Buck2Drv <1:0>			11 : stronger 10 : middle 01 : weaker 00 : weakest							



Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0		
		Function			HVBuck f	sw Selection	on / Error I	nformatior	1			
A15	0x0F	Meaning	HVBuc <1	k_OSC :0>	Err_Base	Err_ HVBuck	Err_LSW	Err_ Buck2	Err_ Buck3	Err_LDO		
		Default	1	1	0	0	0	0	0	0		
		Read/Write	R/W	R/W	R	R	R	R	R	R		
			Define HVBuck switching frequency									
нч	Buck_OS	C <1:0>	11 : 2MH 10 : 2MH 01 : 1MH 00 : 500k	11 : 2MHz 10 : 2MHz 01 : 1MHz 00 : 500kHz								
Err Base								recycle to				
1 : Happen VINUVLO or VINOVP or OTP or sequence time too lo 0 : Didn't happen VINUVLO, VINOVP, OTP and sequence time too							oo long ne too long	9				
			Mark HV power on	Buck prote sequence	ection happ e	pen, reset	when ENA	A = <0> ar	nd Hiccup	recycle to		
		UCK	1 : Happe 0 : Didn't	1 : Happen HVBuck UVP or OCP 0 : Didn't happen HVBuck UVP and OCP								
		Λ/	Mark LS power on	W protect	ion happeı ə	n, reset w	hen ENA	= <0> and	d Hiccup	recycle to		
	EII_LS	/v	1 : Happen LSW UVP or OCP 0 : Didn't happen LSW UVP and OCP									
	Err Due	1.0	Mark Buo	ck2 protect	ction happe	en, reset v	vhen ENA	= <0> an	d Hiccup	recycle to		
	EII_BUC	κz	1 : Happe 0 : Didn't	en Buck2 happen B	UVP or OC uck2 UVP	P and OCP						
		1-0	Mark Bud power on	ck3 protect	ction happe	en, reset v	vhen ENA	= <0> an	d Hiccup	recycle to		
1 : Happen Buck3 UVP or OCP 0 : Didn't happen Buck3 UVP and OCP												
		0	Mark LDO protection happen, reset when $ENA = \langle 0 \rangle$ and Hiccup recycle to power on sequence									
		0	1 : Happen LDO UVP or OCP 0 : Didn't happen LDO UVP and OCP									

Address Name	Register Address	Description	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0		
A16	0x10	Function	Disable Normal Read / Reload Default Setting / Error Function Information									
		Meaning	DIS_NR	RELOAD	Reserved	Err_ UVLO2	Err_OVP	Err_OTP	Err_UVP	Err_OCP		
		Default	0	0	0	0	0	0	0	0		
		Read/Write	R/W	R/W	R	R	R	R	R	R		
DIS_NR			Disable normal read control									
			1 : Didn't load normal read data while power on (ENA = Hi) again. Hold original register setting of sRG0x00 to sRG0x0E and sRG0x0F <7:6>. 0 : Enable normal read while power on (ENA = Hi), reset register sRG0x00 to sRG0x0E and sRG0x0F <7:6>									
			Reload default register setting control									
RELOAD			<ul> <li>1 : Reload normal read result into register table and can't write register when RELOAD = &lt;1&gt;</li> <li>0 : register can be wrote</li> </ul>									
Err_UVLO2			Mark UVLO2 protection happen, reset when $ENA = \langle 0 \rangle$ or hiccup recycle to power on sequence									
			1 : Happen UVLO2 0 : Didn't happen UVLO2									
Err_OVP			Mark VINOVP protection happen, reset when $ENA = \langle 0 \rangle$ or hiccup recycle to power on sequence									
			1 : Happen VINOVP 0 : Didn't happen VINOVP									
Err_OTP			Mark OTP protection happen, reset when ENA = <0> or hiccup recycle to power on sequence									
			1 : Happen OTP 0 : Didn't happen OTP									
Err_UVP			Mark UVP protection happen, reset when ENA = <0>									
			1 : Happen UVP 0 : Didn't happen UVP									
			Mark OCP protection happen, reset when ENA = <0>									
Err_OCP		1 : Happen OCP 0 : Didn't happen OCP										



#### **Protections List**

	Protection Type	Threshold (Typical Value)	Mask Time	Protection Method	Reset Method		
VIN	UVLO2	VIN < 3.9V	32µs	Disable all channels	Hiccup protection, restart if VIN > 4.4V and EN = Hi		
	OVP	VIN > 15.5V	5ms	Disable all channels	Hiccup protection, restart if VIN < 13.5V and EN = Hi		
	OCP	PMOS current > 3A	10ms	Cycle-by-Cycle detection then disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
CH1	UVP	VOUT1 < VOUT1 x 0.5 (50%)	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
	VOUT1 OVP	VOUT1 > 5.5V	No mask	Disable CH1	Hiccup Until fail event to be solved		
CH2	OCP	PMOS current > 1.3A		Cycle-by-Cycle detection then disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
	UVP	VOUT2 < VOUT2 x 0.5 (50%)	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
СНЗ	OCP	PMOS current > 1.3A	10ms	Cycle-by-Cycle detection then disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
	UVP	VOUT3 < VOUT3 x 0.5 (50%)	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
	OCP	PMOS current > 0.75A	10ms*	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
CH4	UVP	VOUT4 < VOUT4 x 0.4 (40%)	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
LSW	Current Limit	NMOS current > 0.75A	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
	UVP	VSWI - VSWO > 0.7V	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
		VSWO < 0.85V	No mask	Disable all channels	Latch-off protection, VDDA < 1.6V or EN = low		
Thermal	Thermal Shutdown	Temperature > 160℃	No mask	Disable all channels	Latch-off protection, EN = High and Temperature < 140℃		

 $^{\ast}$  When current limit is working, VOUT4 drops and UVP trigger less than 10ms.

#### **Thermal Considerations**

The junction temperature should never exceed the absolute maximum junction temperature  $T_{J(MAX)}$ , listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula :

 $\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = (\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}) / \theta_{\mathsf{J}\mathsf{A}}$ 

where  $T_{J(MAX)}$  is the maximum junction temperature,  $T_A$  is the ambient temperature, and  $\theta_{JA}$  is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 150°C. The junction-to-ambient thermal resistance,  $\theta_{JA}$ , is highly package dependent. For a WQFN-24L 4x4 package, the thermal resistance,  $\theta_{JA}$ , is 28°C/W on a standard JEDEC 51-7 high effective-thermalconductivity four-layer test board. The maximum power dissipation at  $T_A = 25^{\circ}C$  can be calculated as below :

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (28^{\circ}C/W) = 4.46W$  for a WQFN-24L 4x4 package.

The maximum power dissipation depends on the operating ambient temperature for the fixed  $T_{J(MAX)}$  and the thermal resistance,  $\theta_{JA}$ . The derating curves in Figure 7 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.



#### Figure 7. Derating Curve of Maximum Power Dissipation

Layout Considerations

For the best performance of the RT2070T, the following PCB layout guidelines must be strictly followed.

- > Place the input and output capacitors as close as possible to the input and output pins respectively for good filtering.
- Keep the main power traces as wide and short as possible.
- The switching node area connected to LX and inductor should be minimized for lower EMI.
- Place the feedback components as close as possible to the FBx pin and keep these components away from the noisy devices.
- Connect the GND and Exposed Pad to a strong ground plane for maximum thermal dissipation and noise protection.
- Directly connect the output capacitors to the feedback network of each channel to avoid bouncing caused by parasitic resistance and inductance from the PCB trace.





LX should be connected to inductor by wide and short trace, keep sensitive components away from this trace.

The exposed pad must be soldered to a large PCB and connected to GND for maximum thermal dissipation.

Place the feedback components as close as possible to the FBx pin and keep away from noisy devices.

Figure 8. PCB Layout Guide

### **Outline Dimension**



Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol		Dimensions	In Millimeters	Dimensions In Inches				
3	упьог	Min	Min Max Min		Max			
A		0.700	0.800	0.028	0.031			
A1		0.000	0.050	0.000	0.002			
A3		0.175	0.250	0.007	0.010			
b		0.180	0.300	0.007	0.012			
D		3.950	4.050	0.156	0.159			
50	Option 1	2.400	2.500	0.094	0.098			
DZ	Option 2	2.650	2.750	0.104	0.108			
E		3.950	4.050	0.156	0.159			
E2	Option 1	2.400	2.500	0.094	0.098			
	Option 2	2.650	2.750	0.104	0.108			
	е	0.5	500	0.0	20			
L		0.350	0.450	0.014	0.018			

W-Type 24L QFN 4x4 Package



### **Footprint Information**



Package		Number of	Footprint Dimension (mm)								Toloropoo	
		Pin	Р	Ax	Ay	Bx	By	С	D	Sx	Sy	TOIEIance
	Option1	- 24	0.50	4.80	4.80	3.10	3.10	0.85	0.30	2.55	2.55	±0.05
V/W/U/AQFIN4 4-24	Option2									2.60	2.60	

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